

Part Number

Customer

Category	Parameter	Specification	Measurement Method	
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	
	2.0	Notch or Flat	Notch	Wafer Vendor
	3.0	Notch Direction	{110} +/- 1 degree	Wafer Vendor
	4.0	Notch Depth Tolerance	1mm, -0mm / + 0.25mm	Wafer Vendor
	5.0	Notch Angle	90 degrees. +5, -1 degree	Wafer Vendor
	6.0	Overall Thickness	667.70 +/- 5.50 μ m	ADE 100%
	7.0	Total Thickness Variation (TTV)	<5.00 μ m	Guaranteed by Process
	8.0	Bow	<60.00 μ m	ADE to ASTM F534, 20%
	9.0	Warp	<60.00 μ m	ADE to ASTM F657, 20%
	10.0	Edge Chips	0	Bright Light, 100% (note 2)
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	FZ	Wafer Vendor
	13.0	Handle Orientation	{111} off 3.5 +/- 0.5 degree	Wafer Vendor
	14.0	Handle Thickness	658.00 +/- 5.00 μ m	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	5000 - 10000 Ohmcm	Wafer Vendor
	18.0	Backside Finish	Lapped and etched with oxide and lasermark	Wafer Vendor
	BuriedOxide	19.0	Oxide Type	Thermal
20.0		Oxide Thickness	22,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
21.0		Oxide formed on	Handle and device Wafer	
DeviceSilicon	22.0	Device Growth Method	CZ	Wafer Vendor
	23.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	24.0	Nominal Thickness	7.50 +/- 0.50 μ m	FTIR, 100% 9-Pt (note3)
	25.0	Distance to device silicon edge from wafer edge	< 2 mm	Guaranteed by Process
	26.0	Device Doping Type	N	Wafer Vendor
	27.0	Device Dopant	Arsenic	Wafer Vendor
	28.0	Device Resistivity	< 0.0025 Ohm-cm	Wafer Vendor
	29.0	Buried Layer Implant	none	implant vendor
	30.0	Voids	0	Bright Light, 100% (note 2)
	31.0	Scratches	0	Bright Light, 100% (note 2)
	32.0	Haze	none	Bright Light, 100% (note 2)

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Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information